

DOCKET NO: 244278US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
HIDETAKA HATTORI, ET AL. : ATTN: APPLICATION DIVISION
SERIAL NO: NEW U.S. PCT APPLN. :
(Based on 10/294,583)
FILED: HEREWITH :
• FOR: POWER SEMICONDUCTOR :
ELEMENT CAPABLE OF
IMPROVING SHORT CIRCUIT
WITHSTAND CAPABILITY WHILE
MAINTAINING LOW ON-
VOLTAGE AND METHOD OF
FABRICATING THE SAME

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

Amendments to the Specification begin on page 2 of this paper.

Amendments to the Abstract begin on page 8 of this paper and include an attached replacement sheet.

Amendments to the Claims are reflected in the listing of claims which begins on page 9 of this paper.

Remarks/Arguments begin on page 11 of this paper.